

Win-Der Lee

List of Publications by Year in descending order

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16
papers

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1478505

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all docs

16
docs citations

16
times ranked

108
citing authors

#	ARTICLE	IF	CITATIONS
1	The effect of adjusting the stroke value of jet dispenser on the performance of glucose biosensor with gold-plated electrode. Proceedings of the Institution of Mechanical Engineers, Part H: Journal of Engineering in Medicine, 2020, 234, 39-47.	1.8	1
2	The Influence of Blood Glucose Meter Resistance Variation on the Performance of a Biosensor with a Gold-Coated Circuit Board. Journal of Sensors, 2019, 2019, 1-8.	1.1	6
3	The Influence of Needle Assembly Sliding of the Jetting Dispenser on the Characteristics of Blood Glucose Test Strip. , 2018, , .		0
4	Applications of Taguchi method to PID control for path tracking of a wheeled mobile robot. , 2018, , .		6
5	Effect of filling pressure in jetting dispenser on the performance of blood glucose test strips using immersion gold-plated printed circuit board. Proceedings of the Institution of Mechanical Engineers, Part H: Journal of Engineering in Medicine, 2018, 232, 779-786.	1.8	4
6	A Novel Optical Morse Code-Based Electronic Lock Using the Ambient Light Sensor and Fuzzy Controller. Applied Sciences (Switzerland), 2017, 7, 140.	2.5	4
7	Investigation of Rapid Low-Power Microwave-Induction Heating Scheme on the Cross-Linking Process of the Poly(4-vinylphenol) for the Gate Insulator of Pentacene-Based Thin-Film Transistors. Materials, 2017, 10, 742.	2.9	1
8	A novel electronic lock using optical Morse code based on the Internet of Things. , 2016, , .		10
9	Poly(4-vinylphenol) gate insulator with cross-linking using a rapid low-power microwave induction heating scheme for organic thin-film-transistors. APL Materials, 2016, 4, 036105.	5.1	14
10	Teflon/SiO ₂ Bilayer Passivation for Improving the Electrical Reliability of Oxide TFTs Fabricated Using a New Two-Photomask Self-Alignment Process. Materials, 2015, 8, 1704-1713.	2.9	19
11	Self-aligned amorphous indium-gallium-zinc-oxide thin-film transistor using a two-mask process without etching-stop layer. , 2014, , .		1
12	Gate Leakage for 28 nm Stacked HfZrO ₂ Dielectric of p-Channel MOSFETs After Decoupled Plasma Nitridation Treatment With Annealing Temperatures. IEEE Transactions on Plasma Science, 2014, 42, 3712-3715.	1.3	7
13	Modification of Early Effect for 28-nm nMOSFETs Deposited With HfZrO ₂ Dielectric After DPN Process Accompanying Nitrogen Concentrations. IEEE Transactions on Plasma Science, 2014, 42, 3747-3750.	1.3	5
14	Gate Leakage Characteristics for 28 nm HfZrO ₂ pMOSFETs After DPN Process Treatment With Different Nitrogen Concentration. IEEE Transactions on Plasma Science, 2014, 42, 3703-3705.	1.3	7
15	A Self-Aligned a-IGZO Thin-Film Transistor Using a New Two-Photo-Mask Process with a Continuous Etching Scheme. Materials, 2014, 7, 5761-5768.	2.9	11
16	Electrical quality of 28nm HK/MG MOSFETs with PDA and DPN treatment. , 2014, , .		0